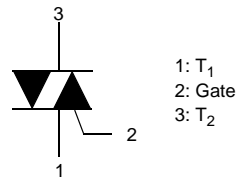
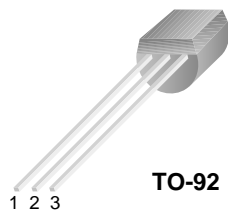


FKN08PN60S

TRIAC (Silicon Bidirectional Thyristor)

Application Explanation

- Switching mode power supply, light dimmer, electric flasher unit, hair drier
- TV sets, stereo, refrigerator, washing machine
- Electric blanket, solenoid driver, small motor control
- Photo copier, electric tool



Absolute Maximum Ratings T_a = 25°C unless otherwise noted

Symbol	Parameter	Value	Rating	Units
V _{DRM} V _{RPM}	Peak Repetitive Off-State Voltage	Sine Wave 50 to 60Hz, Gate Open	600	V
I _{T (RMS)}	RMS On-State Current	Commercial frequency, sine full wave 360° conduction, T _c = 70 °C	0.8	A
I _{TSM}	Surge On-State Current	Sinewave half cycle, peak value, non-repetitive	60Hz 8	A
I ² t	I ² t for Fusing	Value corresponding to halfwave, surge on-state current, tp=8.33ms	0.26	A ² s
P _{GM}	Peak Gate Power Dissipation		5	W
P _{G (AV)}	Average Gate Power Dissipation		0.1	W
V _{GM}	Peak Gate Voltage		5	V
I _{GM}	Peak Gate Current		1	A
T _J	Junction Temperature		- 40 ~ 125	°C
T _{STG}	Storage Temperature		- 40 ~ 125	°C

Thermal Characteristics

Symbol	Parameter	Value	Units
R _{θJC}	Thermal Resistance, Junction to Case ^(note1)	45	°C/W
R _{θJA}	Thermal Resistance, Junction to Ambient ^(note2)	160	°C/W

Note1: Infinite cooling condition.

Note2: JESD51-10 (Test Borad: FR4 3.0"*4.5"*0.062", Minimum land pad)

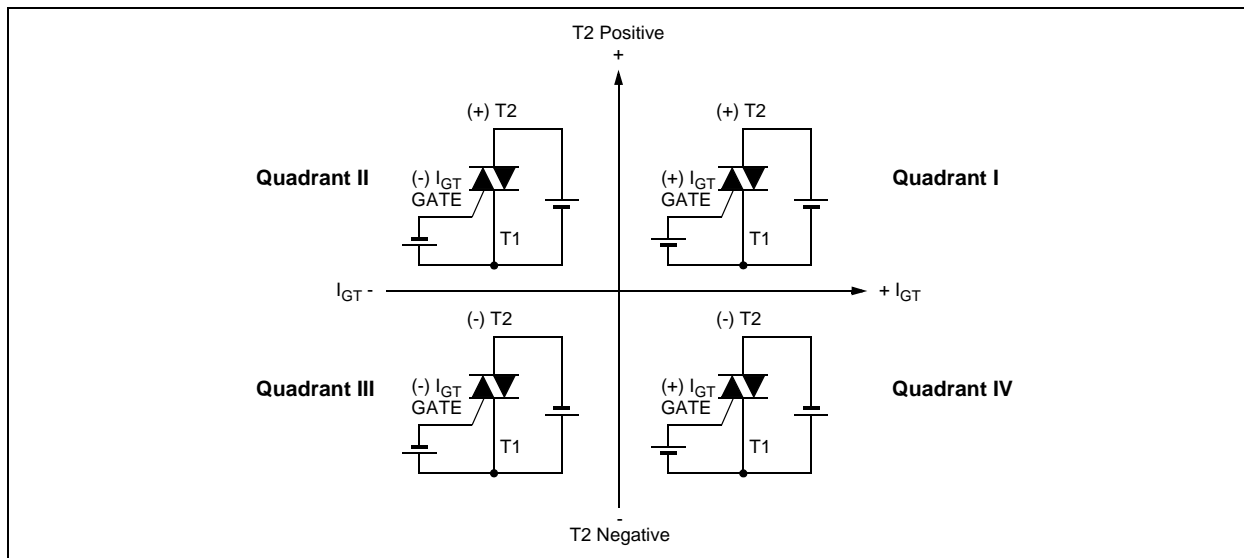
Electrical Characteristics T_C = 25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units		
I _{DRM} I _{RRM}	Repetitive Peak Off-State Current	V _{DRM} /V _{RRM} applied	-	-	100	μA		
V _{TM}	On-State Voltage	T _C =25°C, I _{TM} =1.12A Instantaneous measurement	-	-	1.8	V		
V _{GT}	Gate Trigger Voltage (Note 2)	I	V _D =12V, R _L =100Ω	T2(+), Gate (+)	-	-	2.0	V
		II		T2(+), Gate (-)	-	-	2.0	V
		III		T2(-), Gate (-)	-	-	2.0	V
I _{GT}	Gate Trigger Current (Note 2)	I	V _D =12V, R _L =100Ω	T2(+), Gate (+)	-	-	5	mA
		II		T2(+), Gate (-)	-	-	5	mA
		III		T2(-), Gate (-)	-	-	5	mA
V _{GD}	Gate Non-Trigger Voltage	T _J =125°C, V _D =1/2V _{DRM}	0.2	-	-	V		
I _H	Holding Current (I, II, III)	V _D = 12V, I _{TM} = 200mA	-	-	15	mA		
I _L	Latching Current	V _D = 12V, I _G = 10mA	I, III	-	-	15	mA	
			II	-	-	20	mA	
dv/dt(s)	Critical Rate of Rise of Off-State Voltage	V _{DRM} = 63% Rated, T _J = 125°C, Exponential Rise	20	-	-	V/μs		
dv/dt(c)	Critical-Rate of Rise of Off-State Commutating Voltage (di/dt=-0.7A/uS)		3.0	-	-	V/μs		

Commutation dv/dt test

V _{DRM} (V)	Test Condition	Commutating voltage and current waveforms (inductive load)
FKN08PN60S	<ol style="list-style-type: none"> Junction Temperature T_J=125°C Rate of decay of on-state commutating current (di/dt)_C Peak off-state voltage V_D = 300V 	<p>The diagram shows three waveforms over time: <ul style="list-style-type: none"> Supply Voltage: A sinusoidal wave crossing zero. Main Current: A current that decays to zero as the supply voltage crosses zero. The rate of decay is labeled (di/dt)_C. Main Voltage: A square wave that transitions from a positive level to a negative level (V_D) during the zero-crossing of the supply voltage. The rate of change of this voltage is labeled (dv/dt)_C. </p>

Quadrant Definitions for a Triac



Package Marking and Ordering Information

Device Marking	Device	Package	Packing	Tape Width	Quantity
K08PN60S	FKN08PN60S	TO-92	BULK	--	--

Typical Performance Characteristics

Figure 1. On-State Characteristics

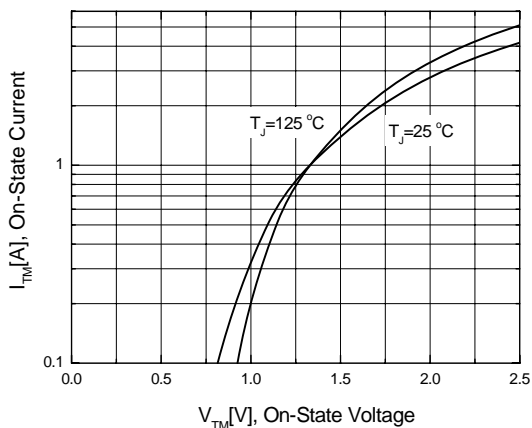


Figure 2. Power Dissipation

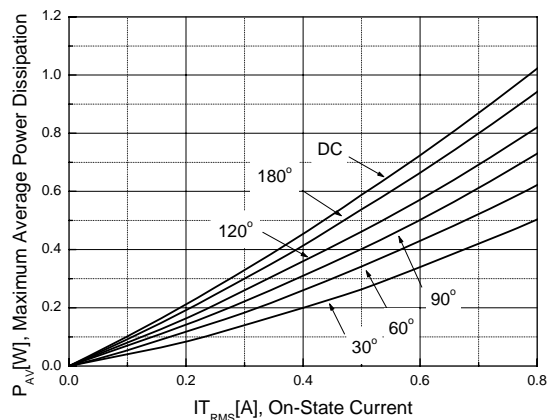


Figure 3. RMS Current Rating

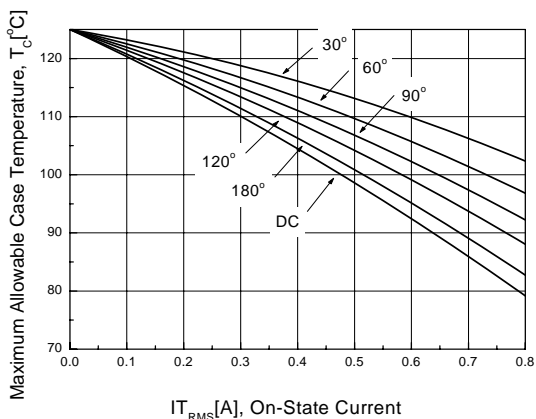


Figure 4. Typical Gate Trigger Current vs Junction Temperature

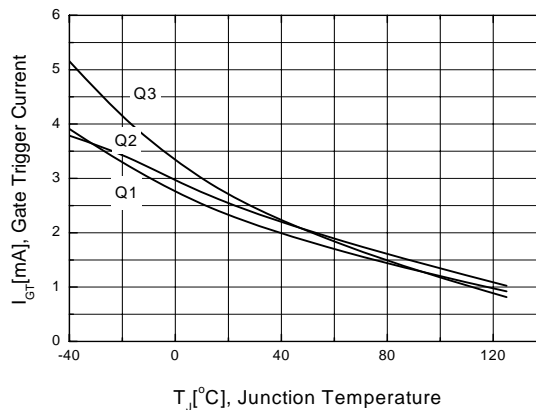


Figure 5. Typical Gate Voltage vs Junction Temperature

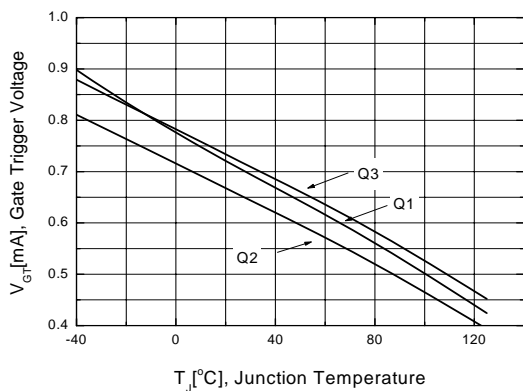
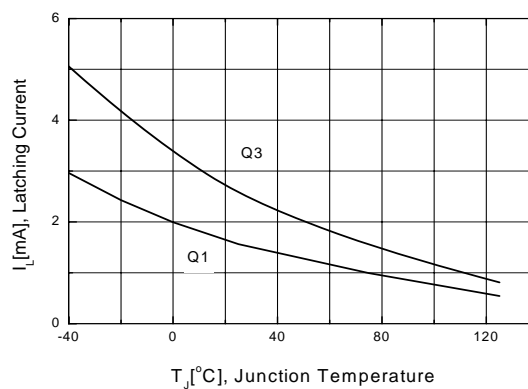


Figure 6. Typical Latching Current vs Junction Temperature



Typical Performance Characteristics (Continued)

Figure7. Typical Holding Current vs Junction Temperature

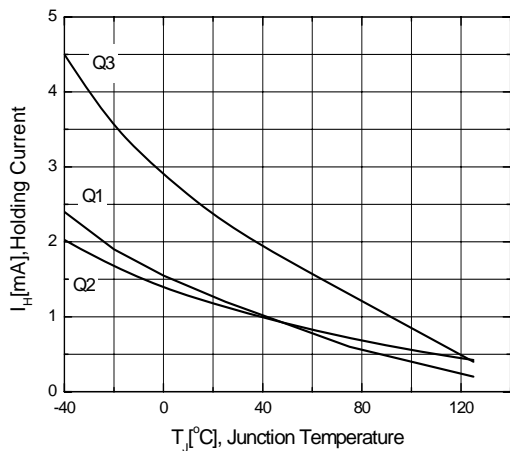
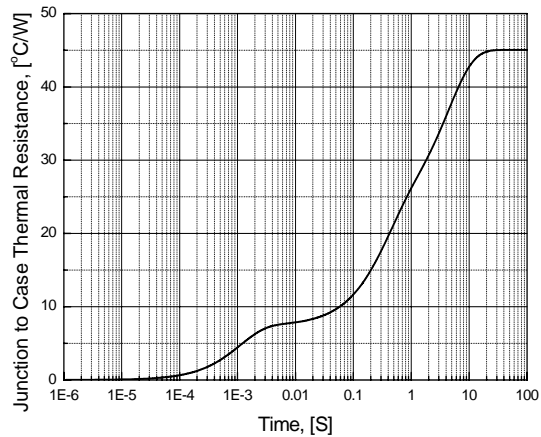
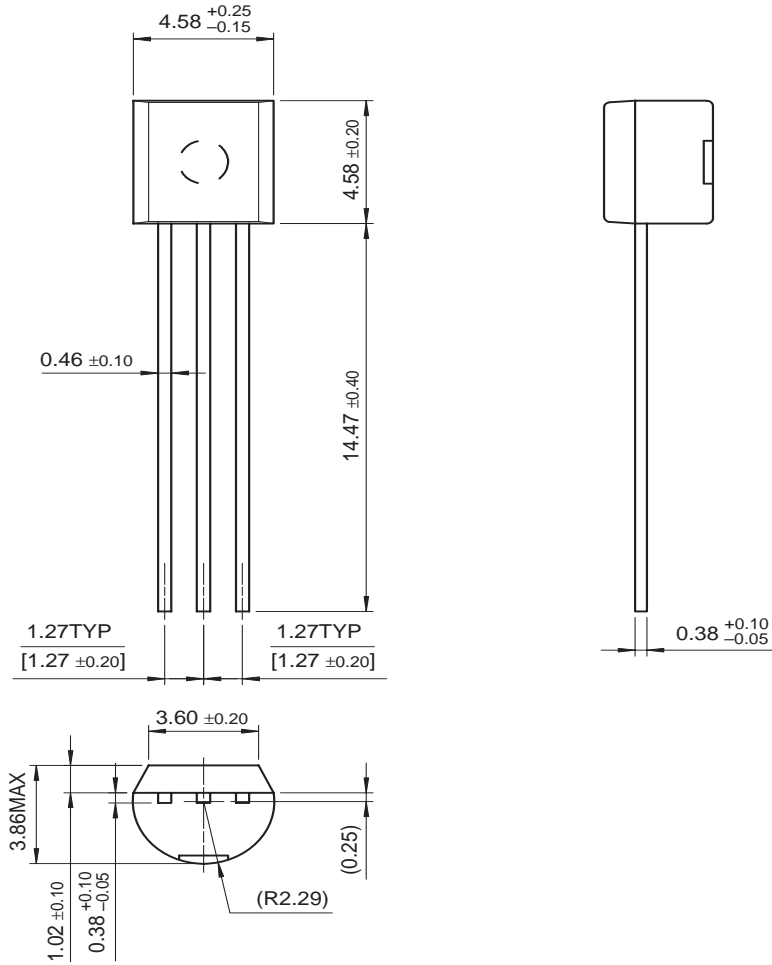


Figure8. Junction to Case Thermal Resistance



Package Dimension

TO-92





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